

BUK7A1R3-100L

N-channel 100V, 1.3m Ω , Standard Level MOSFET in CCPAK1212

26 August 2025

Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 12 low ohmic split-gate technology, for ultra-low $R_{DS(on)}$ capability, housed in a CCPAK1212 (SOT8000A) package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and reliability.

2. Features and benefits

Fully automotive qualified to AEC-Q101:

175 °C rating suitable for thermally demanding automotive environments.

Trench 12 split-gate trench technology:

- Reduced cell pitch enables enhanced power density resulting in lower conduction losses.
- Fast and efficient switching with optimal damping for low spiking and improved switching efficiency.

CCPAK mounting base

 Large cross-sectional area of exposed drain tab for excellent thermal dissipation and low steady state thermal resistance.

CCPAK gull-wing leads:

- · High Board Level Reliability (BLR), pins absorbing mechanical stress during thermal cycling.
- Visual (AOI) soldering inspection, no need for expensive x-ray equipment.

CCPAK copper clip technology:

- Low transient thermal resistance and package inductance.
- High maximum current capability and improved current spreading on silicon die.

3. Applications

- Light-electric / Electric vehicle applications
- 48V to 12V DC-DC Converters
- Synchronous rectifier for On-Board Charging (OBC) systems
- 48V Traction Inverters
- 48V Belt Starter Generator (BSG)
- Battery Management Systems

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	355	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	935	W
Tj	junction temperature		-55	-	175	°C



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'	'	
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 9</u>	-	1.02	1.3	mΩ
	resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 10	-	2.4	3	mΩ
Dynamic cl	haracteristics			'		
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	14	46	106	nC
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 ^{\circ}\text{C}$	-	228	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source		
3	S	source		
4	S	source	12 11 10 9 8 7	
5	S	source	<u> </u>	
6	S	source		D
7	D	drain		
8	D	drain		G T T
9	D	drain		mbb076 S
10	D	drain	1 2 3 4 5 6 CCPAK1212 (SOT8000A)	
11	D	drain	301 ARTIZIZ (3010000A)	
12	D	drain		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
BUK7A1R3-100L	CCPAK1212	Plastic, surface mounted copper clip package (CCPAK1212); 13 terminals; 2.0 mm pitch, 12 mm x 12 mm x 2.5 mm body	SOT8000A		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7A1R3-100L	X7A1R310L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	935	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	355	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[1]	-	355	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	2236	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain o	diode				•	
Is	source current	T _{mb} = 25 °C		-	355	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	2236	Α
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 99 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 175 μ s; Fig. 4	[2]	-	1126	mJ
I _{AS}	non-repetitive avalanche current	V_{sup} = 100 V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; R_{GS} = 50 Ω ; $Fig. 4$	[2]	-	99	A

- [1] Continous current is limited by package
- [2] Protected by 100% test

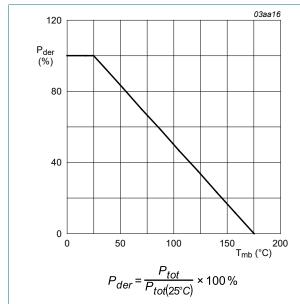
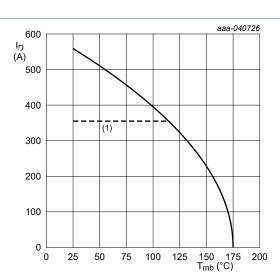


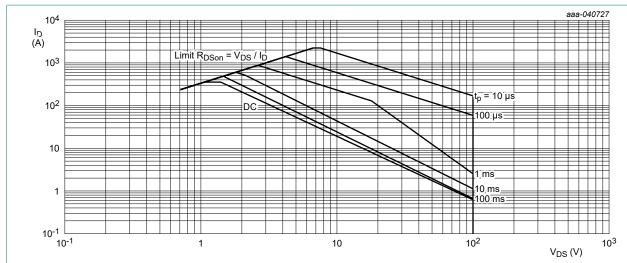
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{\rm GS} \ge 10~{\rm V}$ (1) 355 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

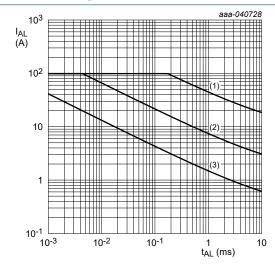
Fig. 2. Continuous drain current as a function of mounting base temperature

3 / 13



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

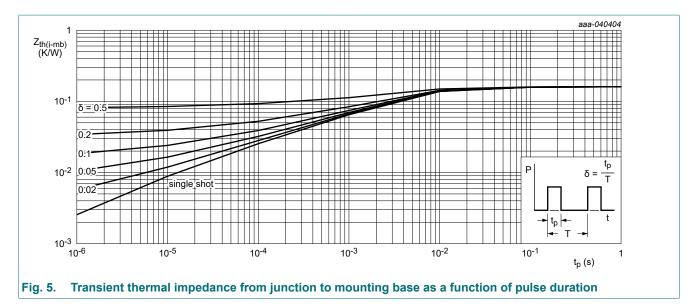
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	0.123	0.16	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	14	-	K/W

[1] Device on 4 layer PCB. Refer to TN00008 for further information.



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C	2	3.08	4	V
, ,	voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _i = 175 °C	-	1.58	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C	-	3.6	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-9.32	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.08	1.6	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 125 °C	-	31	160	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 9$	-	1.02	1.3	mΩ
	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 10	-	1.7	2.1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 10	-	2.4	3	mΩ
		V _{GS} = 7 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 9</u>	-	1.28	1.92	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.54	1.08	2.16	Ω
Dynamic cha	racteristics		'			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	128	255	383	nC
		I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V; T_j = 25 °C	-	228	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 50 V; V _{GS} = 10 V;	46	76.5	107	nC
Q _{GS(th)}	pre-threshold gate- source charge	T _j = 25 °C; <u>Fig. 11</u> ; <u>Fig. 12</u>	-	51	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	25.4	-	nC
Q_{GD}	gate-drain charge		14	46	106	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 50 V; T _j = 25 °C; Fig. 11; Fig. 12	-	4.4	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz;	10901	18168	25436	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>	2494	4157	6652	pF
C _{rss}	reverse transfer capacitance		9	92	239	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$	-	67	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	63	-	ns
t _{d(off)}	turn-off delay time	1	-	157	-	ns
t _f	fall time	1	-	84	-	ns
Source-drain	diode		1	1	1	1
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 14</u>	-	0.76	1	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}		$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	62	-	ns
Q _r	recovered charge	V _{DS} = 50 V; T _j = 25 °C; <u>Fig. 15</u>	-	74	-	nC

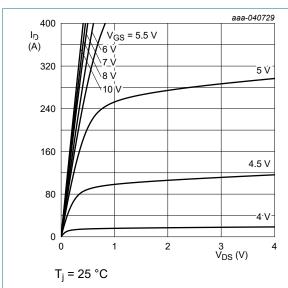


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

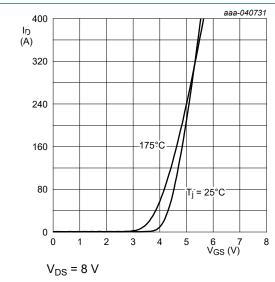


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

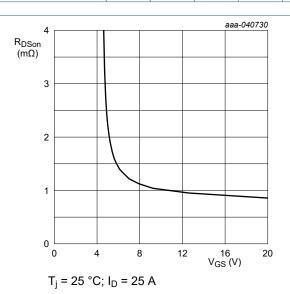


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

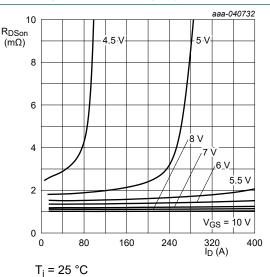


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

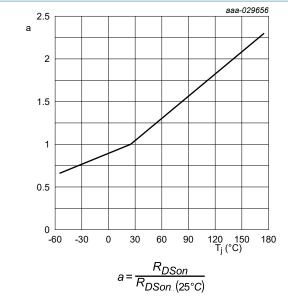


Fig. 10. Normalized drain-source on-state resistance factor as a function of junction temperature

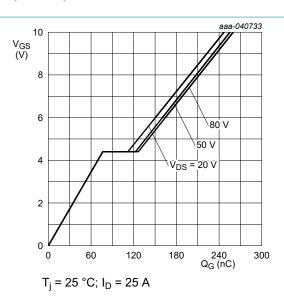


Fig. 11. Gate-source voltage as a function of gate charge; typical values

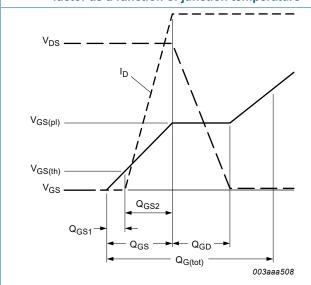
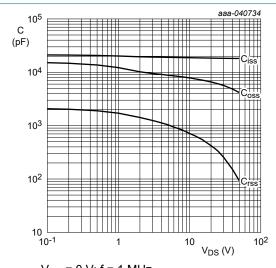


Fig. 12. Gate charge waveform definitions



 $V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

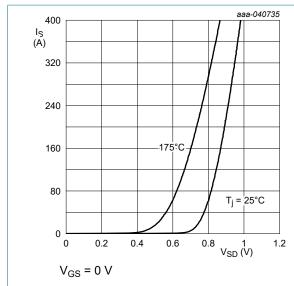


Fig. 14. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

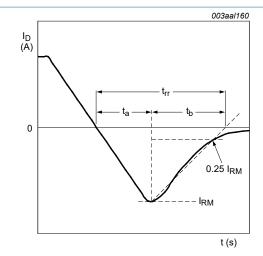


Fig. 15. Reverse recovery timing definition

11. Package outline

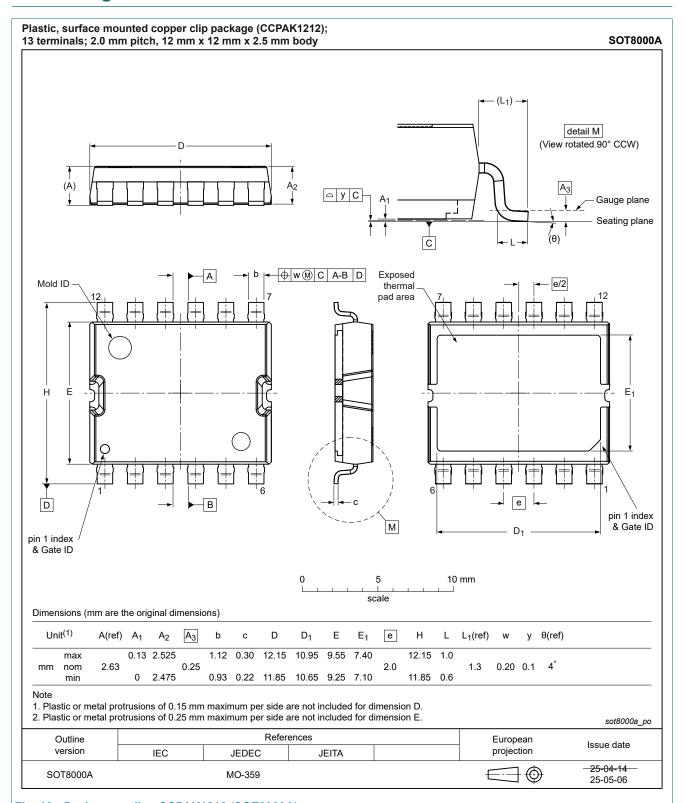
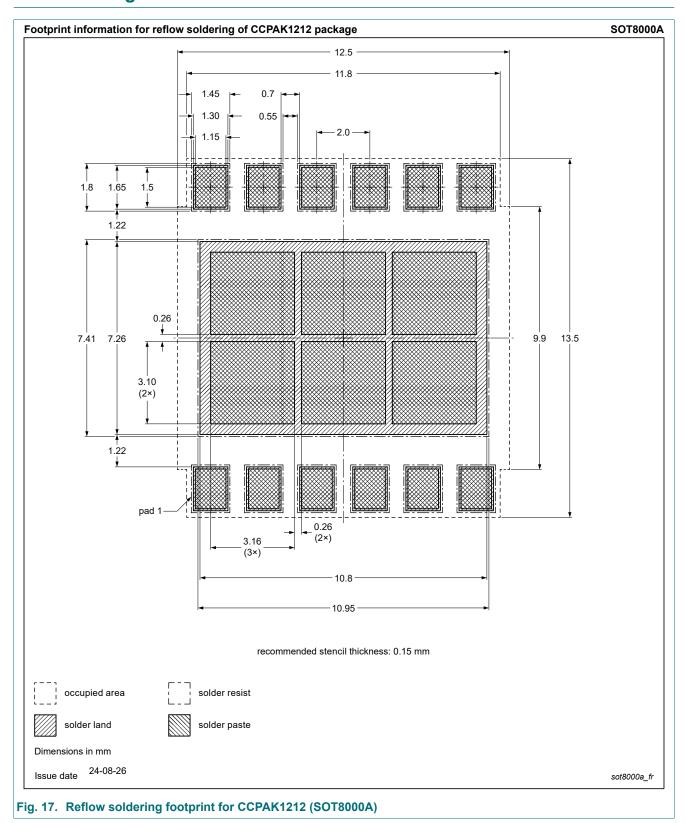


Fig. 16. Package outline CCPAK1212 (SOT8000A)

12. Soldering



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	4
10	. Characteristics	6
11.	Package outline	10
12	. Soldering	11
13	Legal information	12

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